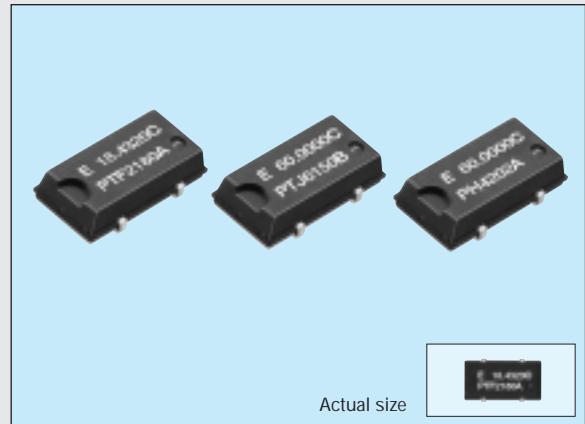


## SMALL SOJ HIGH-FREQUENCY CRYSTAL OSCILLATOR

**SG-636 series**

- A small SMD that enables high-density mounting.
- A general-purpose device with builtin heat-resisting cylindrical AT-cut crystal and allowing almost the same temperature condition for soldering as SMD IC.
- Low current consumption.
- Provided with output enable function.
- 3.3V operation, stand-by function available.



Actual size

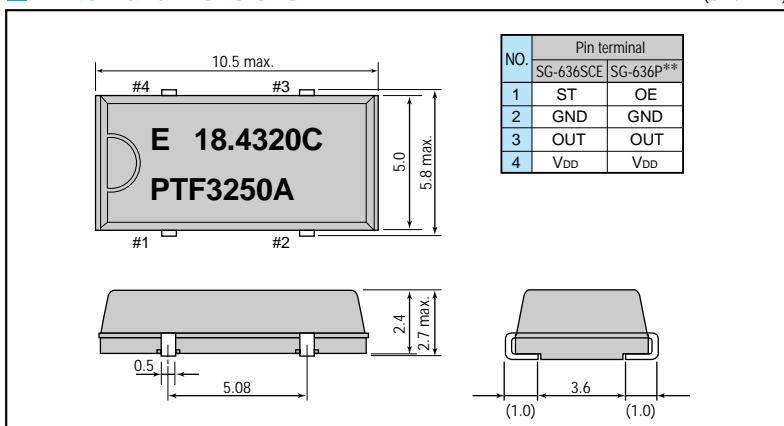
**■ Specifications (characteristics)**

Item		Symbol	SG-636PTF	SG-636PTJ	SG-636PH	SG-636SCE/PCE	Remarks
			Specifications				
Output frequency range		f <sub>0</sub>	2.21675 MHz to 41.0000 MHz	41.0001 MHz to 70.0000 MHz	2.21675 MHz to 40.0000 MHz		
Power source voltage	Max. supply voltage	V <sub>DD</sub> -GND	-0.5V to +7.0V	-0.3V to +7.0V	-0.5V to +7.0V		
	Operating voltage	V <sub>DD</sub>		5.0V ±0.5V		3.3V ±0.3V	
Temperature range	Storage temperature	T <sub>STG</sub>		-55°C to +100°C			Stored as bare product after unpacking
	Operating temperature	T <sub>OPR</sub>		-20°C to +70°C			
Soldering condition		T <sub>SOL</sub>		Twice at under 260°C within 10 sec. or under 230°C within 3 min.			
Frequency stability		Δf/f <sub>0</sub>		C: ±100ppm			-10°C to +70°C
Current consumption		I <sub>OP</sub>	17mA max.	35mA max.	9mA max.		No load condition
Duty	C-MOS level	t <sub>w/t</sub>	40% to 60%	—	40% to 60%	45% to 55%	C-MOS load: 1/2V <sub>DD</sub> level
	TTL level		45% to 55%			—	TTL load: 1.4V level
Output voltage		V <sub>OH</sub>	V <sub>DD</sub> -0.4V min.	2.4V min.	V <sub>DD</sub> -0.4V min.		
		(I <sub>OH</sub> )	-8mA	-400μA	-4mA		
		V <sub>OL</sub>		0.4V max.			
		(I <sub>OL</sub> )	16mA	8mA	4mA		
Output load condition (fan out)	C-MOS	C <sub>L</sub>	50pF max.	15pF	20pF max. (≤ 55 MHz) 15pF max. (> 55 MHz)	30pF max.	
	TTL	N	10TTL max.	5TTL max.	5 LS TTL max.	—	C <sub>L</sub> ≤15pF
Output enable/disable input voltage		V <sub>IH</sub>	2.0V min.	3.5V min.	2.0V min.	0.8V <sub>DD</sub> min.	I <sub>IH</sub> =1μA max. (OE=V <sub>DD</sub> ) PTF, PTJ, PH
		V <sub>IL</sub>	0.8V max.	1.5 max.	0.8V max.	0.2V <sub>DD</sub> max.	I <sub>IL</sub> =100μA min. (OE=GND) PTF, PH -500μA min. (OE=GND) PTJ
Output disable current		I <sub>OE</sub>	10mA max.	28mA max.	20mA max.	5mA max.	OE=GND, ST=GND 2μA max. (SCE)
Output rise time	C-MOS level	t <sub>THL</sub>	7ns max.	—	5ns max.		C-MOS load: 20%→80%V <sub>DD</sub>
	TTL level		5ns max.		—		TTL load: 0.4V→2.4V
Output fall time	C-MOS level	t <sub>THL</sub>	7ns max.	—	5ns max.		C-MOS load: 80%→20%V <sub>DD</sub>
	TTL level		5ns max.		—		TTL load: 2.4V→0.4V
Oscillation start up time		t <sub>osc</sub>	4ms max.	10ms max.	4ms max.		Time at 4.5V to be 0 sec.
Aging		f <sub>a</sub>		±5ppm/year max.			Ta=25°C, V <sub>DD</sub> =5V, first year
Shock resistance		S.R.		±20ppm max.			Three drops on a hard board from 75 cm or excitation test with 3000G x 0.3ms x 1/2 sine wave in 3 directions

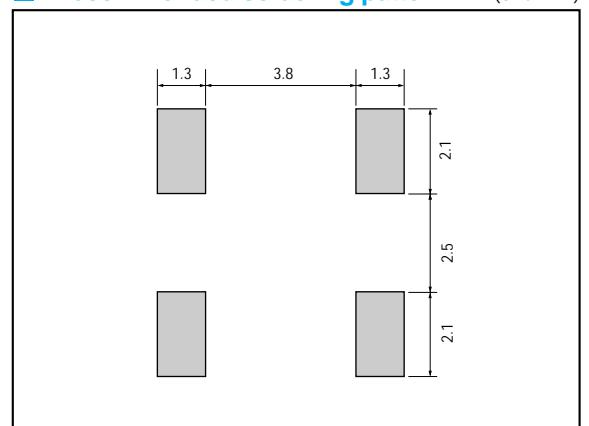
Note: • Unless otherwise stated, characteristics (specifications) shown in the above table are based on the rated operating temperature and voltage condition.

• External by-pass capacitor is required.

• There are some cases that a parts of the cylindrical capsule of quartz unit expose on the surface of the molding material.

**■ External dimensions**

(Unit: mm)

**■ Recommended soldering pattern**

(Unit: mm)